

INFORMATION DISCLOSURE CITATION IN AN APPLICATION  (PTO-1449)		ATTY. DOCKET NO. 57810-031		SERIAL NO.			
		APPLICANT Tatsuya KUNISATO, et al.					
		FILING DATE February 25, 2002		GROUP			
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
g	6,015,979	1/18/2000	Sugiura et al.	257	86		
↓	6,051,849	4/18/2000	Davis et al.	257	76		
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
cc	2000-164989	6/16/2000	Japan (w/ English Abstract)				
↓	2000-269144	9/29/2000	Japan (w/ English Abstract)				
↓	10-312971	11/24/1998	Japan (w/ English Abstract)				
↓	2000-21789	1/21/2000	Japan (w/ English Abstract)				
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
cc	S. Nakamura et al., "Long lifetime violet InGaN/GaN/AlGaIn-based semiconductor lasers", Journal of Oyo Denshi Bussei Bunkakai, Vol. 4, (1998), pp. 53-58 and 210-215.						
cc	Akira Usui et al., "Thick GaN Epitaxial Growth with Low Dislocation Density by Hydride Vapor Phase Epitaxy", Jpn. J. Appl. Phys. Vol. 36 (1997), pp. L899-L902.						
EXAMINER			DATE CONSIDERED				
C. Lam			06-26-2003				

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.